

Superconducting properties of MgB₂ probed by radiation-induced disordering

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(Dated: February 1, 2008)

The electrical resistivity ρ and upper critical field H_{c2} were measured in MgB₂ disordered by nuclear reactor neutrons. We found that superconducting temperature T_c decreases under irradiation from 40 to 5 K. Despite strong disordering (more than 10 dpa (displacements per atom)), the initial crystal structure is preserved. The residual resistivity ρ_0 increases from 0.35 to 2 m Ω cm while $-dH_{c2}/dT$ remains approximately unchanged ($-dH_{c2}/dT \approx 0.5$ T/K), and such behavior may be interpreted as decrease in the density of electronic states.

With the discovery of superconductivity (SC) in binary compound MgB₂ with relatively high $T_c \approx 40$ K [1], a question arises about the possible origin of SC in such a simple compound. It is well known that high density of electronic states at the Fermi level $N(E_F)$, similar to soft phonon frequencies, can lead to enhancement of T_c in BCS phonon-mediate superconductivity [2], while some form of exotic coupling can take place in this case. One of the ways to determine the nature of coupling is to study the response of SC on disordering induced by irradiation with high-energy particles.

Disordering of intermetallic compounds, such as A15 (Nb₃Sn, V₃Si), with high $N(E_F)$ leads to decrease of T_c from 15 - 20 K to 1 - 3 K due to drop in $N(E_F)$ at disordering [3]. In low- T_c compounds (Mo₃Si and Mo₃Ge), irradiation leads to increase of T_c (from 1.5 to 7 K) due to rise in $N(E_F)$ as well as due to softening of phonon frequencies. It means that individual features of the electronic structure disappear under disordering, and the superconducting properties of the disordered compounds become similar to the properties of amorphous materials obtained by various methods.

The influence of disordering on SC of high- T_c compounds is not similar to that of A15: irradiation leads to very fast degradation of SC ($T_c = 0$) [4]. Although the origin of T_c -degradation is not clear (because the mechanism of SC in high- T_c is unknown), there is a significant difference between intermetallic compounds and more exotic materials in the response to disordering.

In this paper we studied the transport properties of polycrystalline samples ($0.05 \cdot 1 \cdot 5$ mm³) irradiated in nuclear reactor IVV-2M at $T \approx 350$ K up to fluences of thermal neutrons $\Phi = 1 \cdot 10^{19}$ cm⁻², and of fast neutrons, to $5 \cdot 10^{18}$ cm⁻² (to the total dose - of more than 10 dpa). The MgB₂ powder was prepared by the technology described in Ref. [5]. The samples were compacted under 9 Gpa at room temperature without any subsequent heat treatment. Such sample preparation produces a stressed

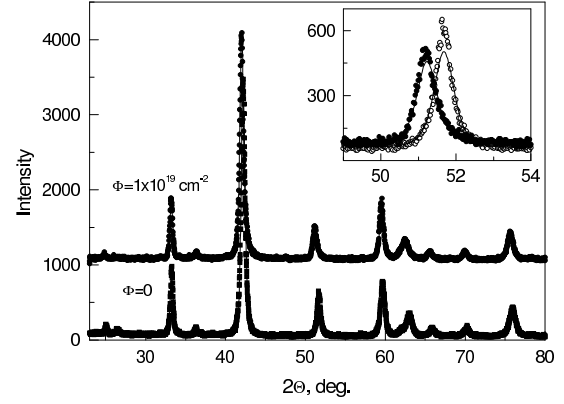


FIG. 1: X-ray diffraction patterns for initial ($\Phi = 0$) and irradiated ($\Phi = 1 \cdot 10^{19}$ cm⁻²) MgB₂ samples.

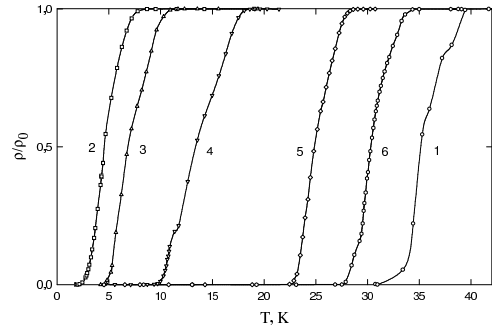


FIG. 2: Resistivity superconducting transition curves for initial (1), irradiated (2) and annealed at 200, 300, 400, 500°C (3-6) MgB₂ samples.

structure, which results in broadening of X-ray peaks (Fig. 1) and resistivity ρ (Fig. 2) and ac-susceptibility χ (Fig. 3) superconducting transitions. However the initial crystal structure (C32) is preserved under irradiation inducing such high damage to the material.

Fig. 1 shows X-ray diffraction patterns (Cu-K α) for the initial and the irradiated samples of MgB₂. The samples contain traces (~ 3 %) of MgO. The structure parameters were refined with Rietveld analysis. Some discrepancy between the measured and the calculated curves

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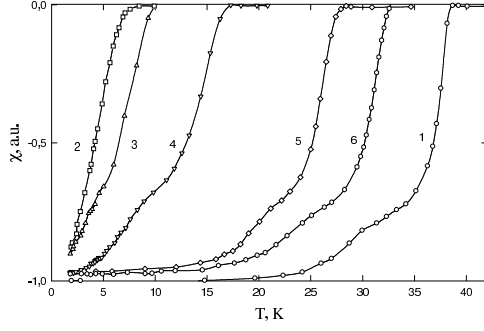


FIG. 3: AC-susceptibility superconducting transition curves for initial (1), irradiated (2) and annealed at 200, 300, 400, 500°C (3-6) MgB₂ samples.

(see the insert in Fig. 3) was connected with the sample texture. Irradiation leads to anisotropic expansion of the crystal lattice (the cell volume increase is about 1.4 %) with faster increase of c , as is well seen in the insert in Fig. 3 and Table I. The broadened diffraction peaks in the initial samples become narrower after irradiation, which is an evidence of partial relief of stress. The Rietveld analysis refinement yields some decrease in the Mg site occupation numbers (if B site occupation is fixed equal to unit), although we do not expect appearance of anti-structural defects because of the difference in the atomic sizes of Mg and B.

TABLE I: Lattice parameters a , c , cell volume V and site occupation number (Mg) for initial and irradiated MgB₂ samples.

	Initial	Irradiated
a , Å	3.0878(2)	3.0953(3)
c , Å	3.5216(4)	3.5533(4)
V , Å ³	29.080(4)	29.482(5)
c/a	1.140	1.148
$N(\text{Mg})$	0.96(4)	0.89(5)

Figs. 2, 3 show transformations of ρ - and χ -transitions in irradiated and annealed samples. There are no essential changes of transition widths under irradiation, which testifies to homogeneous distribution of radiation defects. Annealing at 500 K recovers 85 % of T_c . The values of the upper critical field H_{c2} determined by half-width of the normal state resistivity show almost the same slope for the initial, irradiated and post-annealed samples (Fig. 4). $H' = -dH_{c2}/dT$ shows low dependence on normal state resistivity ρ_0 (see the insert in Fig. 4). The resistivity $\rho(T)$ increases after irradiation, decreases after annealing up to 300° C and grows again at subsequent annealing reaching 4 mΩ cm (Fig. 5). We consider that such a behavior of $\rho(T)$ may be partly due to intergrain transport,

therefore $\rho(T)$ is not completely an intrinsic property. As is expected, H' within the dirty limit should increase with the decrease in the mean free path of electron un-

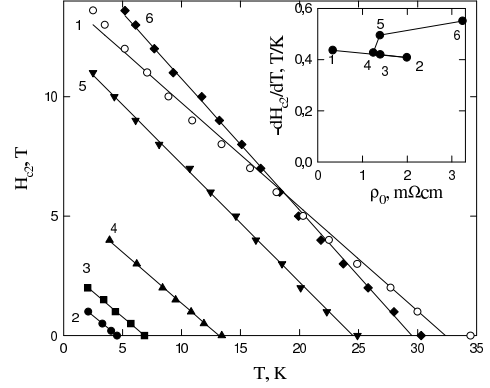


FIG. 4: Upper critical field H_{c2} vs. temperature T for initial (1), irradiated (2) and annealed at 200, 300, 400, 500°C (3-6) MgB₂ samples. Insert shows $-dH_{c2}/dT$ as a function of normal state resistivity ρ_0 .

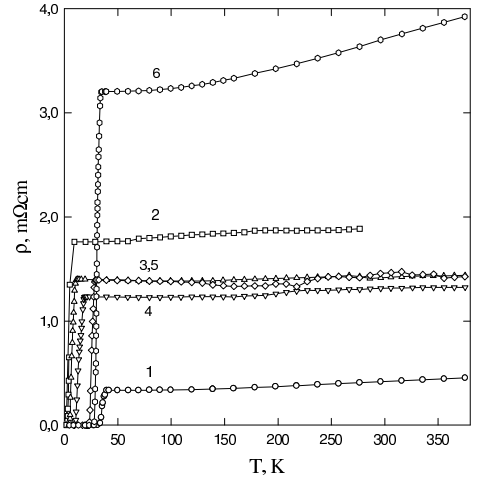


FIG. 5: Temperature dependences of resistivity ρ for initial(1), irradiated(2) and annealed at 200, 300, 400, 500°C(3-6) MgB₂ samples

der disordering, therefore the small change in H' may be interpreted as the decrease of $N(E_F)$ with decreasing T_c . It may be supposed that, similar to A15 compounds, there is a fine structure in $N(E)$ in the vicinity of the Fermi level, which is smeared under radiation-induced disordering.

Work supported by the Russian State contracts Nos 107-1(00)-P, 107-19(00)-P, 108-31(00)-P, the Russian State Program of Support to Leading Scientific Schools (Project No. 00-15-96581) and RFBR Grant No. 00-02-16877.

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